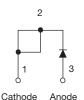
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Fast Soft Recovery Rectifier Diode, 10 A





PRODUCT SUMMARY					
Package	TO-220FP				
I _{F(AV)}	10 A				
V _R	1000 V, 1200 V				
V _F at I _F	1.33 V				
I _{FSM}	140 A				
t _{rr}	80 ns				
T _J max.	150 °C				
Diode variation	Single die				
Snap factor	0.6				

FEATURES

- Glass passivated pellet chip junction
- 150 °C max. operation junction temperature
 Designed and qualified according to JEDEC[®]-JESD 47
- Fully isolated package (V_{INS} = 2500 V_{BMS})
- UL E78996 approved
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

These devices are intended for use in output rectification and freewheeling in inverters, choppers and converters as well as in input rectification where severe restrictions on conducted EMI should be met.

DESCRIPTION

The VS-10ETF1..FP... fast soft recovery rectifier series has been optimized for combined short reverse recovery time and low forward voltage drop.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
V _{RRM}		1000 to 1200	V			
I _{F(AV)}	Sinusoidal waveform	10	٨			
I _{FSM}		140	– A			
t _{rr}	1 A, 100 A/μs	80	ns			
V _F	10 A, T _J = 25 °C	1.33	V			
TJ		-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA			
VS-10ETF10FPPbF, VS-10ETF10FP-M3	1000	1100	4			
VS-10ETF12FPPbF, VS-10ETF12FP-M3	1200	1300	4			

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum average forward current	I _{F(AV)}	T_{C} = 95 °C, 180° conduction half sine wave	10			
Maximum peak one cycle	I	10 ms sine pulse, rated V _{RRM} applied	115	А		
non-repetitive surge current	IFSM	10 ms sine pulse, no voltage reapplied	140			
Martine and 121 for the start	l ² t	10 ms sine pulse, rated V _{RRM} applied	66	A ² s		
Maximum I ² t for fusing I ² t		10 ms sine pulse, no voltage reapplied	94	A-2		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied	940	A²√s		

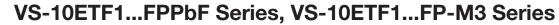
Revision: 11-Feb-16

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Document Number: 94093

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V _{FM}	10 A, T _J = 25 °C		1.33	V
Forward slope resistance	r _t	T.I = 150 °C		22.9	mΩ
Threshold voltage	V _{F(TO)}	1J = 150 C		0.96	V
Maximum reverse leakage aurrent	$I_{RM} = \frac{T_J = 25 \text{ °C}}{T_J = 150 \text{ °C}}$	T _J = 25 °C	V Detect V	0.1	mA
Maximum reverse leakage current		T _J = 150 °C	$V_R = Rated V_{RRM}$	4	ША

RECOVERY CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	· .	
Reverse recovery time	t _{rr}	L at 10 A	310	ns	I _{FM}	
Reverse recovery current	I _{rr}	I _F at 10 A _{pk} 25 A/μs	4.7	А		
Reverse recovery charge	Q _{rr}	25 °C	1.05	μC	$\frac{\text{dir}}{\text{dt}}$	
Snap factor	S		0.6		I IRM(REC)	

THERMAL - MECH	THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +150	°C	
Maximum thermal resistance junction to case		R _{thJC}	DC operation	2.5		
Maximum thermal resistance junction to ambient		R _{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5		
Approvimate weight				2	g	
Approximate weight				0.07	oz.	
minimum				6 (5)	kgf ⋅ cm	
Mounting torque maxim	maximum			12 (10)	(lbf ⋅ in)	
Marking device			Case style TO-220 FULL-PAK	10ETF10FP 10ETF12FP		



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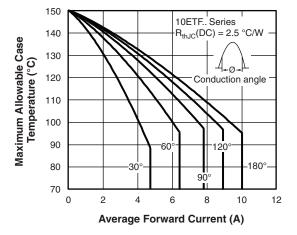


Fig. 1 - Current Rating Characteristics

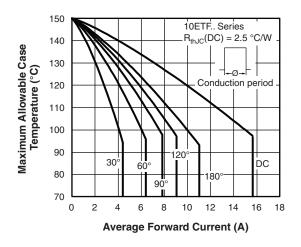


Fig. 2 - Current Rating Characteristics

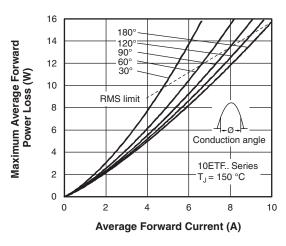


Fig. 3 - Forward Power Loss Characteristics

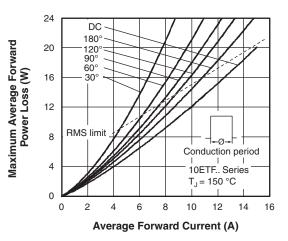


Fig. 4 - Forward Power Loss Characteristics

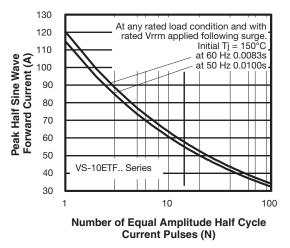
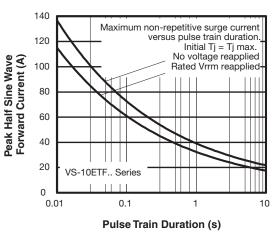


Fig. 5 - Maximum Non-Repetitive Surge Current





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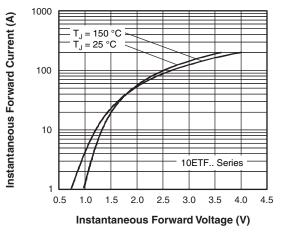


Fig. 7 - Forward Voltage Drop Characteristics

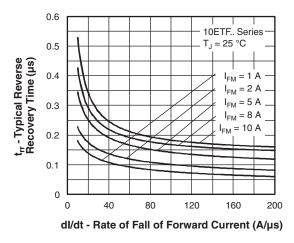


Fig. 8 - Recovery Time Characteristics, $T_J = 25 \ ^{\circ}C$

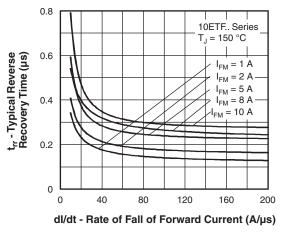
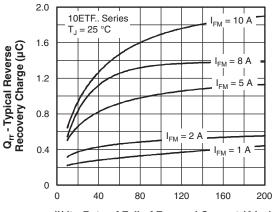


Fig. 9 - Recovery Time Characteristics, T_J = 150 $^\circ\text{C}$



dl/dt - Rate of Fall of Forward Current (A/µs)

Fig. 10 - Recovery Charge Characteristics, T_J = 25 °C

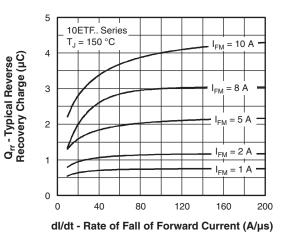


Fig. 11 - Recovery Charge Characteristics, $T_J = 150 \ ^{\circ}C$

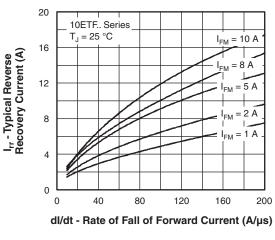


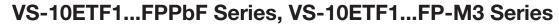
Fig. 12 - Recovery Current Characteristics, T_J = 25 °C

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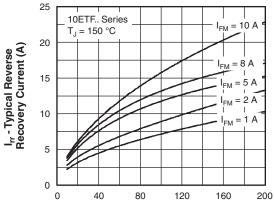
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dl/dt - Rate of Fall of Forward Current (A/µs)

Fig. 13 - Recovery Current Characteristics, T_J = 150 °C

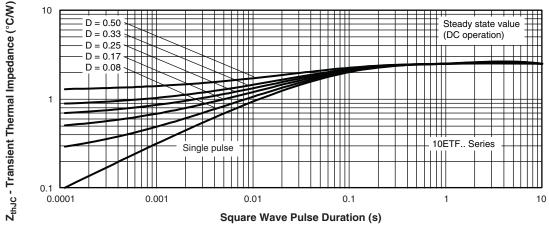


Fig. 14 - Thermal Impedance Z_{thJC} Characteristics



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ORDERING INFORMATION TABLE

Device code	VS-	10	Е	т	F	12	FP	PbF
		2	3	4	5	6	7	8
	1 - 2 - 3 -	Vishay Semiconductors product Current rating (10 = 10 A) Circuit configuration: E = single diode						
	4 -		Package: T = TO-220					
	5 -	Тур	Type of silicon: E = fast soft receivery rectifier					
	6 - 7 -	Voli FUL	Voltage code x 100 = V_{RRM} $02 = 200 \text{ V}$ FULL-PAK $06 = 600 \text{ V}$					
	8 -		Environmental digit: • PbF = lead (Pb)-free and RoHS-compliant					

• -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-10ETF10FPPbF	50	1000	Antistatic plastic tubes				
VS-10ETF10FP-M3	50	1000	Antistatic plastic tubes				
VS-10ETF12FPPbF	50	1000	Antistatic plastic tubes				
VS-10ETF12FP-M3	50	1000	Antistatic plastic tubes				

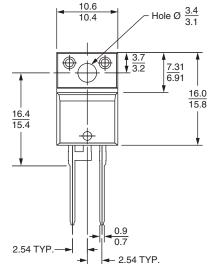
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95005			
Port marking information	TO-220 FP PbF	www.vishay.com/doc?95009			
Part marking information	TO-220 FP -M3	www.vishay.com/doc?95440			



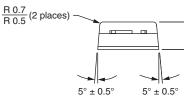
Outline Dimensions

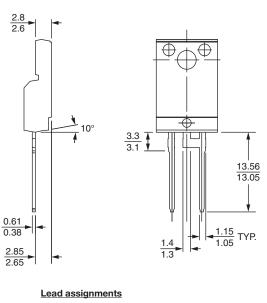
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DIMENSIONS in millimeters



 $\frac{4.8}{4.6}$





<u>Diodes</u> 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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